

TRANSI STOR (NPN)	SOT-23 Plastic-Encapsulate Transistors
 	

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	30			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	15			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA, IC=0	5			V
Collector cut-off current	ICBO	VCB= 20 V , IE=0			0.1	μA
Collector cut-off current	ICEO	VCE= 15V , IB=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 3V , IC=0			0.1	μA
DC current gain	hFE	VCE= 5V, IC= 1mA	70		200	
Collector-emitter saturation voltage	VCE(sat)	IC= 10mA, IB= 1mA			0.5	V
Base-emitter saturation voltage	VBE(sat)	IC= 10 mA, IB= 1mA			1.4	V
Transition frequency	fT	VCE= 5V, IC= 5mA f=400MHz		80		MHz

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

